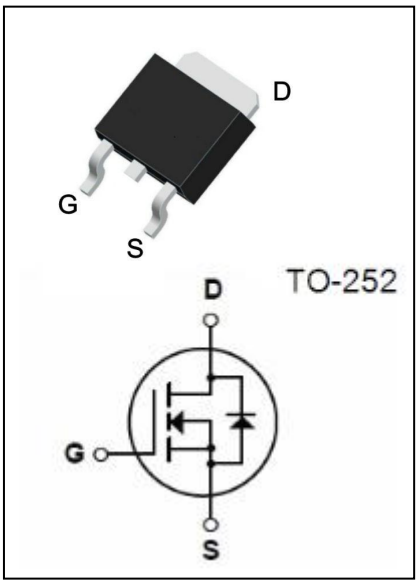
GXD65R540

650V N-Channnel Super Junction Power MOSFET



●Features：

- 8.0A, 650V, $R_{DS(on)(Typ)}$ =480mΩ@V_{GS}=10V
- Ultra Low Gate Charge
- Ultra Low C_{rss}
- 100% Avalanche Tested
- Fast Switching
- Improved dv/dt Capability

●Application:

- High Frequency Switching Mode Power Supply
- Active Power Factor Correction

Absolute Maximum Ratings(Tc=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	650	V
V_{GSS}	Gate-Source Voltage	±30	V
I_D	Drain Current - Continuous(Tc=25°C)	8.0*	A
	- Continuous(Tc=100°C)	5.2*	A
I_{DM}	Drain Current -Pulsed (Note1)	24*	A
P_D	Power Dissipation(T_C =25°C)	80	W
	-Derate above 25°C	0.64	W/°C
E_{AS}	Single Pulsed Avalanche Energy (Note2)	185	mJ
I_{AR}	Avalanche Current (Note1)	4	A
E_{AR}	Repetitive Avalanche Energy, t_{AR} limited by T_{jmax} (Note1)	0.4	mJ
dv/dt	Drain Source voltage slope, V_{DS}≤480V	50	V/ns
dv/dt	Reverse diode dv/dt , V_{DS}≤480V, I_{SD}≤I_D	15	V/ns
Tj	Operating Junction Temperature	150	°C
Tstg	Storage Temperature Range	-55 to+150	°C

* Drain Current Limited by Maximum Junction Temperature.

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.56	°C /W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	62	°C /W

Electrical Characteristics(Tc=25°C unless otherwise noted)

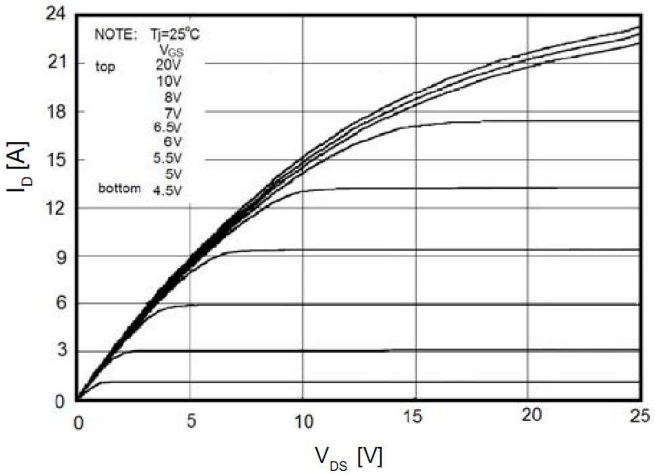
Symbol	Parameter	Test Conditons	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-source Breakdown Voltage	V_{GS}=0V ,I_D=250μA	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=650V,V_{GS}=0V	--	--	1	μA
		V_{DS}=650V,Tc=125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current,Forward	V_{GS}=+30V, V_{DS}=0V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current,Reverse	V_{GS}=-30V, V_{DS}=0V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS}=10 V, I_D=4.0A	--	480	540	mΩ
g_{FS}	Forward Transconductance	V_{DS}=20 V, I_D=4.0A	--	6.0	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=50V,V_{GS}=0V, f=1.0MHz	--	680	--	pF
C_{oss}	Output Capacitance		--	58	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4.0	--	pF
Q_g	Total Gate Charge	V_{DS} = 480V, I_D =8 A, V_{GS} = 10 V	--	14.5	--	nC
Q_{gs}	Gate-Source Charge		--	2.8	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC
R_G	Intrinsic gate resistance	f=1MHz open drain		2		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 380V, I_D = 4 A, R_G =12 Ω, V_{GS}=10 V	--	5.5	--	ns
t_r	Turn-On Rise Time		--	3.5	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	55	--	ns
t_f	Turn-Off Fall Time		--	6.5	--	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_{SD}	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I_{SDM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	24	A
V_{SD}	Drain-Source Diode Forward Voltage	T_J = 25°C , V_{GS} =0V,I_{SD}=8.0A	--	--	1.2	V
t_{rr}	Reverse Recovery Time	T_J = 25°C , I_F=8.0A, dI_F /dt=100A/μs	--	220	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.2	--	μC
I_{rrm}	Peak Reverse Recovery Current		--	20	--	A

Notes:

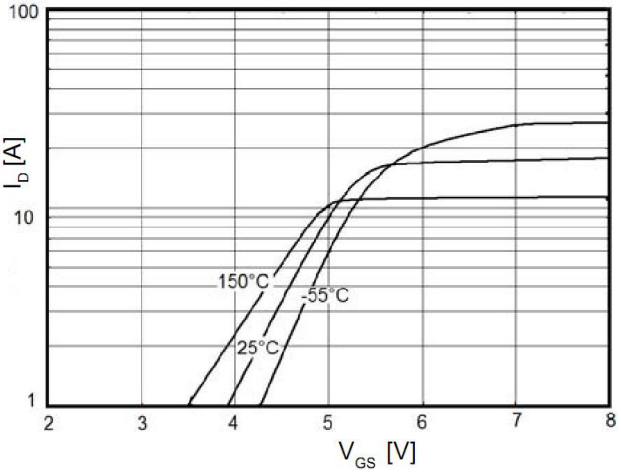
1、Repetitive Rating:Pulse Width Limited by Maximum Junction Temperature.

2、T_J = 25°C ,V_{DD} = 50V, V_G =10V, R_G = 25 Ω.

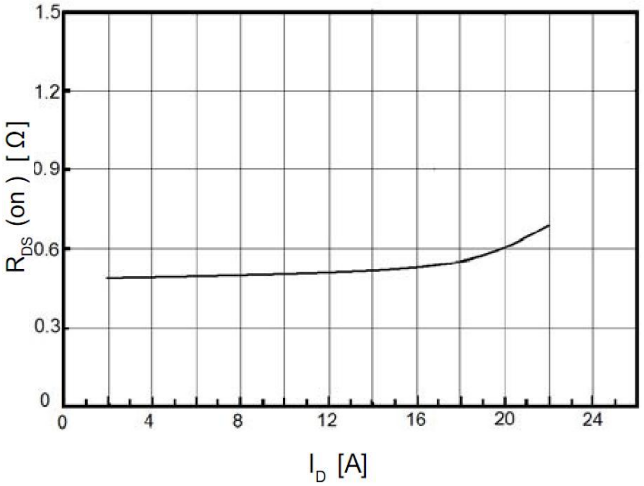
On-Regin Characteristics



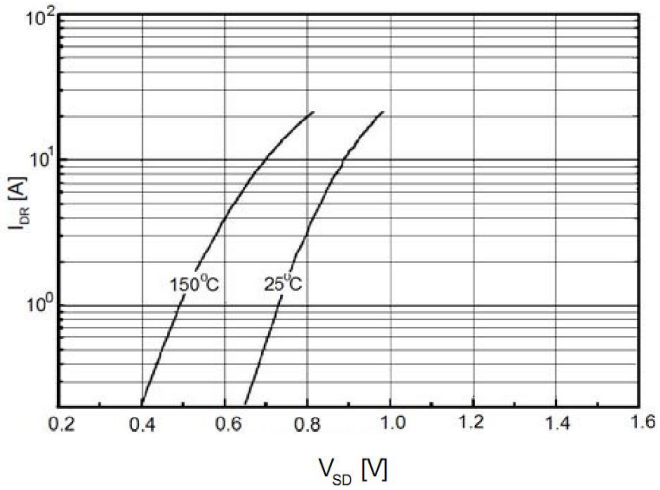
Transfer Characteristics



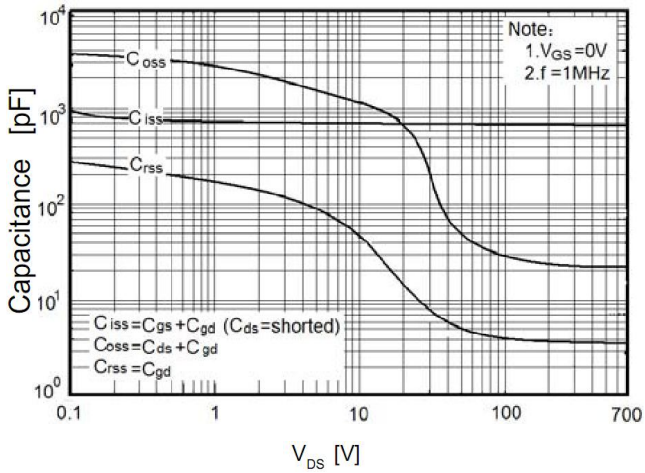
On-Resistance Variation vs. Drain Current and Gate Voltage



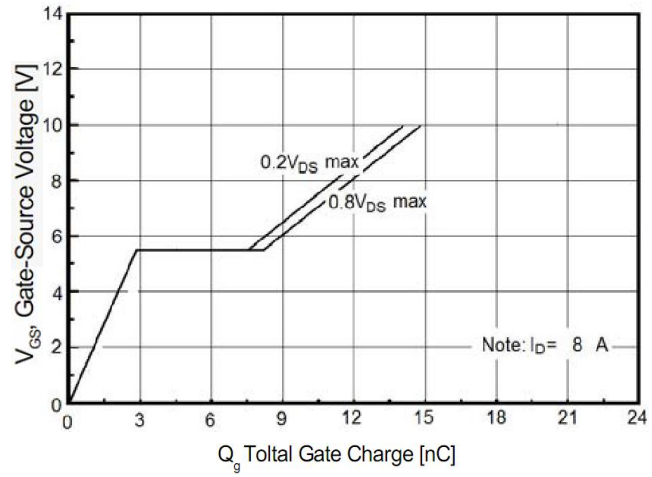
Body Diode Forward Voltage Variation vs. Source Current and Temperature



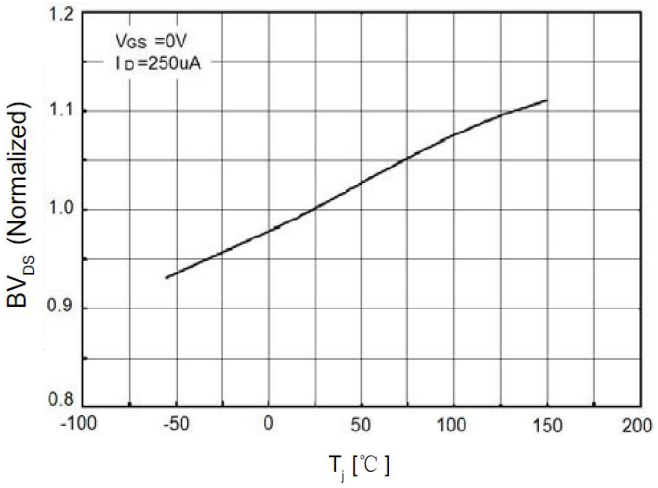
Capacitance Characteristics



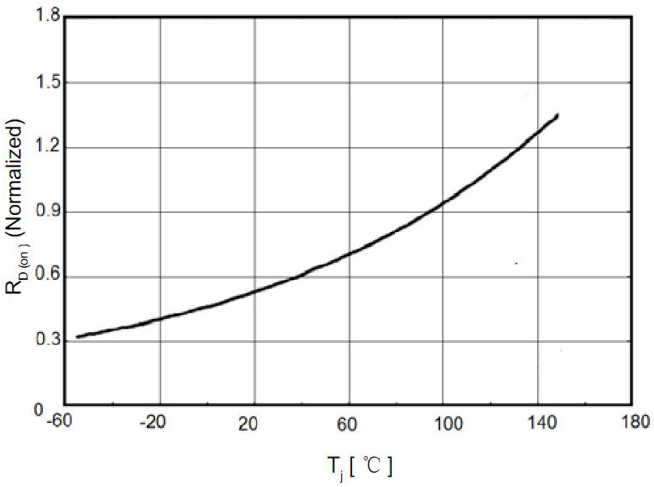
Gate Charge Characteristics



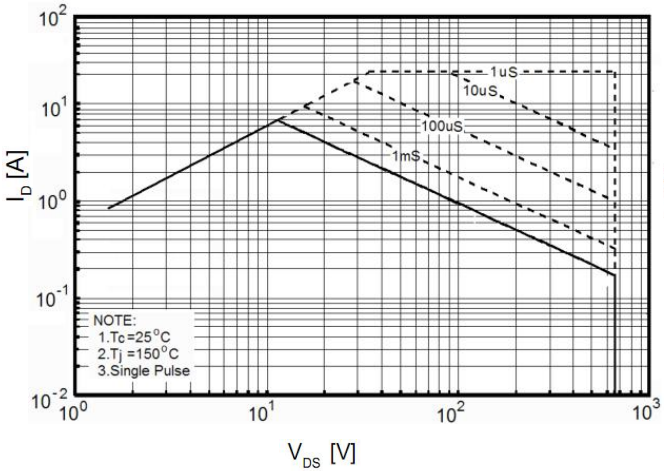
Breakdown Voltage Variation vs. Temperature



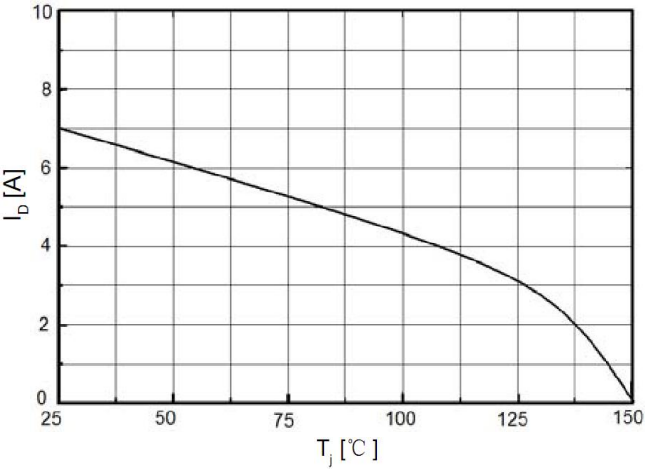
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area



Maximum Drain Current Vs. Case Temperature



TO-252 Package Dimensions

UNIT：mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	6.40		6.60	D	2.90		3.10
A1	5.20		5.40	D1	0.45		0.55
A2	4.40		4.60	D2	0.45		0.55
A3	4.40		4.60	e		2.30	
A4	0		0.15	E	2.20		2.40
A5	4.65		4.95	F	0.45		0.55
B	5.90		6.20	G		1.70	
B1	1.57		1.77	L	1.40		1.60
C	0.90		0.96	θ（度）	0		10.00